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Embedded - System On Chip (SoC): The Heart of Modern Embedded Systems

Embedded - System On Chip (SoC) refers to an integrated circuit that consolidates all the essential components of a computer system into a single chip. This includes a microprocessor, memory, and other peripherals, all packed into one compact and efficient package. SoCs are designed to provide a complete computing solution, optimizing both space and power consumption, making them ideal for a wide range of embedded applications.

What are Embedded - System On Chip (SoC)?

System On Chip (SoC) integrates multiple functions of a computer or electronic system onto a single chip. Unlike traditional multi-chip solutions. SoCs combine a central

Details	
Product Status	Active
Architecture	MCU, FPGA
Core Processor	Quad ARM® Cortex®-A53 MPCore™ with CoreSight™, Dual ARM®Cortex™-R5 with CoreSight™, ARM Mali™-400 MP2
Flash Size	-
RAM Size	256KB
Peripherals	DMA, WDT
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, MMC/SD/SDIO, SPI, UART/USART, USB OTG
Speed	500MHz, 600MHz, 1.2GHz
Primary Attributes	Zynq®UltraScale+™ FPGA, 926K+ Logic Cells
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	1760-BBGA, FCBGA
Supplier Device Package	1760-FCBGA (42.5x42.5)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xczu17eg-1ffvd1760i

Table 1: **Absolute Maximum Ratings[1] *(Cont'd)***

Symbol	Description	Min	Max	Units
Video Codec Unit				
V_{CCINT_VCU}	Internal supply voltage for the video codec unit.	–0.500	1.000	V
PL System Monitor				
V_{CCADC}	PL System Monitor supply relative to GNDADC.	0.500	2.000	V
V_{REFP}	PL System Monitor reference input relative to GNDADC.	0.500	2.000	V
Temperature				
T_{STG}	Storage temperature (ambient).	–65	150	°C
T_{SOL}	Maximum soldering temperature.[12]	–	260	°C
T_j	Maximum junction temperature.[12]	–	125	°C

Notes:

1. Stresses beyond those listed under Absolute Maximum Ratings might cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those listed under Operating Conditions is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods of time might affect device reliability.
2. When operating outside of the recommended operating conditions, refer to Table 6, Table 7, and Table 8 for maximum overshoot and undershoot specifications.
3. V_{CCINT_IO} must be connected to V_{CCBRAM}.
4. V_{CCAUX_IO} must be connected to V_{CCAUX}.
5. The lower absolute voltage specification always applies.
6. If V_{CCO} is 3.3V, the maximum voltage is 3.4V.
7. For I/O operation, see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).
8. AC coupled operation is not supported for RX termination = floating.
9. For GTY transceivers, DC coupled operation is not supported for RX termination = GND.
10. DC coupled operation is not supported for RX termination = programmable.
11. For more information on supported GTH or GTY transceiver terminations see the *UltraScale Architecture GTH Transceiver User Guide* (UG576) or *UltraScale Architecture GTY Transceiver User Guide* (UG578).
12. For soldering guidelines and thermal considerations, see the *Zynq UltraScale+ MPSoC Packaging and Pinout Specifications* (UG1075).

Recommended Operating Conditions

Table 2: **Recommended Operating Conditions(1)(2)**

Symbol	Description	Min	Typ	Max	Units
Processor System					
$V_{CC\_PSINTFP}$(3)	PS full-power domain supply voltage.	0.808	0.850	0.892	V
	For -1LI and -2LE (V_{CCINT} = 0.72V) devices: PS full-power domain supply voltage.	0.808	0.850	0.892	V
	For -3E devices: PS full-power domain supply voltage.	0.873	0.900	0.927	V
$V_{CC\_PSINTLP}$	PS low-power domain supply voltage.	0.808	0.850	0.892	V
	For -1LI and -2LE (V_{CCINT} = 0.72V) devices: PS low-power domain supply voltage.	0.808	0.850	0.892	V
	For -3E devices: PS low-power domain supply voltage.	0.873	0.900	0.927	V
V_{CC_PSAUX}	PS auxiliary supply voltage.	1.710	1.800	1.890	V
$V_{CC\_PSINTFP\_DDR}$(3)	PS DDR controller and PHY supply voltage.	0.808	0.850	0.892	V
	For -1LI and -2LE (V_{CCINT} = 0.72V) devices: PS DDR controller and PHY supply voltage.	0.808	0.850	0.892	V
	For -3E devices: PS DDR controller and PHY supply voltage.	0.873	0.900	0.927	V
V_{CC_PSADC}	PS SYSMON ADC supply voltage relative to GND_PSADC.	1.710	1.800	1.890	V
V_{CC_PSPLL}	PS PLL supply voltage.	1.164	1.200	1.236	V
$V_{PS\_MGTRAVCC}$	PS-GTR supply voltage.	0.825	0.850	0.875	V
$V_{PS\_MGTRAVTT}$	PS-GTR termination voltage.	1.746	1.800	1.854	V
V_{CCO_PSDDR}(4)	PS DDR I/O supply voltage.	1.06	–	1.575	V
$V_{CC\_PSDDR\_PLL}$	PS DDR PLL supply voltage.	1.710	1.800	1.890	V
V_{CCO_PSIO}(5)	PS I/O supply.	1.710	–	3.465	V
V_{PSIN}	PS I/O input voltage.	–0.200	–	V_{CCO_PSIO} + 0.200	V
	PS DDR I/O input voltage.	–0.200	–	V_{CCO_PSDDR} + 0.200	
V_{CC_PSBATT}(6)	PS battery-backed RAM and battery-backed real-time clock (RTC) supply voltage.	1.200	–	1.500	V
Programmable Logic					
V_{CCINT}	PL internal supply voltage.	0.825	0.850	0.876	V
	For -1LI and -2LE (V_{CCINT} = 0.72V) devices: PL internal supply voltage.	0.698	0.720	0.742	V
	For -3E devices: PL internal supply voltage.	0.873	0.900	0.927	V
V_{CCINT_IO}(7)	PL internal supply voltage for the I/O banks.	0.825	0.850	0.876	V
	For -1LI and -2LE (V_{CCINT} = 0.72V) devices: PL internal supply voltage for the I/O banks.	0.825	0.850	0.876	V
	For -3E devices: PL internal supply voltage for the I/O banks.	0.873	0.900	0.927	V
V_{CCBRAM}	Block RAM supply voltage.	0.825	0.850	0.876	V
	For -3E devices: block RAM supply voltage.	0.873	0.900	0.927	V
V_{CCAUX}	Auxiliary supply voltage.	1.746	1.800	1.854	V

Table 2: **Recommended Operating Conditions[1][2]** ***(Cont'd)***

Symbol	Description	Min	Typ	Max	Units
V_{CCO}[8]	Supply voltage for HD I/O banks.	1.140	–	3.400	V
	Supply voltage for HP I/O banks.	0.950	–	1.900	V
V_{CCAUX_IO}[9]	Auxiliary I/O supply voltage.	1.746	1.800	1.854	V
V_{IN}[10]	I/O input voltage.	–0.200	–	V_{CCO} + 0.200	V
I_{IN}[11]	Maximum current through any PL or PS pin in a powered or unpowered bank when forward biasing the clamp diode.	–	–	10	mA
GTH or GTY Transceiver					
$V_{MGTAVCC}$[12]	Analog supply voltage for the GTH or GTY transceiver.	0.873	0.900	0.927	V
$V_{MGTAVTT}$[12]	Analog supply voltage for the GTH or GTY transmitter and receiver termination circuits.	1.164	1.200	1.236	V
$V_{MGTVCCAUX}$[12]	Auxiliary analog QPLL voltage supply for the transceivers.	1.746	1.800	1.854	V
$V_{MGTAVTTRCAL}$[12]	Analog supply voltage for the resistor calibration circuit of the GTH or GTY transceiver column.	1.164	1.200	1.236	V
VCU					
V_{CCINT_VCU}	Internal supply voltage for the VCU.	0.825	0.850	0.876	V
	For -1LI and -2LE (V_{CCINT} = 0.72V) devices: Internal supply voltage for the VCU.	0.825	0.850	0.876	V
	For -3E devices: Internal supply voltage for the VCU.	0.873	0.900	0.927	V

Table 2: **Recommended Operating Conditions[1][2]** ***(Cont'd)***

Symbol	Description	Min	Typ	Max	Units
PL System Monitor					
V_{CCADC}	PL System Monitor supply relative to GNDADC.	1.746	1.800	1.854	V
V_{REFP}	PL System Monitor externally supplied reference voltage relative to GNDADC.	1.200	1.250	1.300	V
Temperature					
T_j[13]	Junction temperature operating range for extended (E) temperature devices.[14]	0	–	100	°C
	Junction temperature operating range for industrial (I) temperature devices.	–40	–	100	°C
	Junction temperature operating range for eFUSE programming.	–40	–	125	°C

Notes:

1. All voltages are relative to GND.
2. For the design of the power distribution system consult *UltraScale Architecture PCB Design Guide* (UG583).
3. $V_{CC\_PSINTFP\_DDR}$ must be tied to $V_{CC\_PSINTFP}$.
4. Includes V_{CCO_PSDDR} of 1.2V, 1.35V, 1.5V at ±5% and 1.1V +0.07V/–0.04V depending upon the tolerances required by specific memory standards.
5. Applies to all PS I/O supply banks. Includes V_{CCO_PSIO} of 1.8V, 2.5V, and 3.3V at ±5%.
6. If the battery-backed RAM or RTC is not used, connect V_{CC_PSBATT} to GND or V_{CC_PSAUX}. The V_{CC_PSAUX} maximum of 1.89V is acceptable on an unused V_{CC_PSBATT}.
7. V_{CCINT_IO} must be connected to V_{CCBRAM}.
8. Includes V_{CCO} of 1.0V (HP I/O only), 1.2V, 1.35V, 1.5V, 1.8V, 2.5V (HD I/O only) at ±5%, and 3.3V (HD I/O only) at +3/–5%.
9. V_{CCAUX_IO} must be connected to V_{CCAUX}.
10. The lower absolute voltage specification always applies.
11. A total of 200 mA per bank should not be exceeded.
12. Each voltage listed requires filtering as described in *UltraScale Architecture GTH Transceiver User Guide* (UG576) or *UltraScale Architecture GTY Transceiver User Guide* (UG578).
13. Xilinx recommends measuring the Tj of a device using the system monitor as described in the *UltraScale Architecture System Monitor User Guide* (UG580). The SYSMON temperature measurement errors (that are described in Table 69 and Table 124) must be accounted for in your design. For example, when using the PL system monitor with an external reference of 1.25V, when SYSMON reports 97°C, there is a measurement error ±3°C. A reading of 97°C is considered the maximum adjusted Tj (100°C – 3°C = 97°C).
14. Devices labeled with the speed/temperature grade of -2LE normally operate under Extended (E) temperature grade specifications with a maximum junction temperature of 100°C. However, E temperature grade devices can operate for a limited time at a junction temperature of 110°C. Timing parameters adhere to the same speed file at 110°C as they do at 100°C, regardless of operating voltage (nominal voltage of 0.85V or a low-voltage of 0.72V). Operation at Tj = 110°C is limited to 1% of the device lifetime and can occur sequentially or at regular intervals as long as the total time does not exceed 1% of the device lifetime.

Power Supply Sequencing

PS Power-On/Off Power Supply Sequencing

The low-power domain (LPD) must operate before the full-power domain (FPD) can function. The low-power and full-power domains can be powered simultaneously. The PS_POR_B input must be asserted to GND during the power-on sequence (see Table 37). The FPD (when used) must be powered before PS_POR_B is released.

To achieve minimum current draw and ensure that the I/Os are 3-stated at power-on, the recommended power-on sequence for the low-power domain (LPD) is listed. The recommended power-off sequence is the reverse of the power-on sequence.

1. $V_{CC\_PSINTLP}$
2. V_{CC_PSAUX}, V_{CC_PSADC}, and V_{CC_PSPLL} in any order or simultaneously.
3. V_{CCO_PSIO}

To achieve minimum current draw and ensure that the I/Os are 3-stated at power-on, the recommended power-on sequence for the full-power domain (FPD) is listed. The recommended power-off sequence is the reverse of the power-on sequence.

1. $V_{CC\_PSINTFP}$ and $V_{CC\_PSINTFP\_DDR}$ driven from the same supply source.
2. $V_{PS\_MGTRAVCC}$ and $V_{CC\_PSDDR\_PLL}$ in any order or simultaneously.
3. $V_{PS\_MGTRAVTT}$ and V_{CCO_PSDDR} in any order or simultaneously.

PL Power-On/Off Power Supply Sequencing

The recommended power-on sequence is V_{CCINT}, V_{CCINT_IO}/V_{CCBRAM}/V_{CCINT_VCU}, V_{CCAUX}/V_{CCAUX_IO}, and V_{CCO} to achieve minimum current draw and ensure that the I/Os are 3-stated at power-on. The recommended power-off sequence is the reverse of the power-on sequence. If V_{CCINT} and V_{CCINT_IO}/V_{CCBRAM} have the same recommended voltage levels, they can be powered by the same supply and ramped simultaneously. V_{CCINT_IO} must be connected to V_{CCBRAM}. If V_{CCAUX}/V_{CCAUX_IO} and V_{CCO} have the same recommended voltage levels, they can be powered by the same supply and ramped simultaneously. V_{CCAUX} and V_{CCAUX_IO} must be connected together. V_{CCADC} and V_{REF} can be powered at any time and have no power-up sequencing requirements.

The recommended power-on sequence to achieve minimum current draw for the GTH or GTY transceivers is V_{CCINT}, $V_{MGTAVCC}$, $V_{MGTAVTT}$ OR $V_{MGTAVCC}$, V_{CCINT}, $V_{MGTAVTT}$. There is no recommended sequencing for $V_{MGTVCCAUX}$. Both $V_{MGTAVCC}$ and V_{CCINT} can be ramped simultaneously. The recommended power-off sequence is the reverse of the power-on sequence to achieve minimum current draw.

If these recommended sequences are not met, current drawn from $V_{MGTAVTT}$ can be higher than specifications during power-up and power-down.

Table 30: **PS DDR Performance *(Cont'd)***

Memory Standard	Package	DRAM Type	Speed Grade						Units
			-3		-2		-1		
			Min	Max	Min	Max	Min	Max	
DDR3	All FFV packages, FBVB900 and SFVC784	Single rank component	664	2133	664	2133	664	2133	Mb/s
		1 rank DIMM[(1)(2)]	664	1866	664	1866	664	1866	Mb/s
		2 rank DIMM[(1)(3)]	664	1600	664	1600	664	1600	Mb/s
	SFVA625	Single rank component	664	1866	664	1866	664	1866	Mb/s
		1 rank DIMM[(1)(2)]	664	1600	664	1600	664	1600	Mb/s
		2 rank DIMM[(1)(3)]	664	1333	664	1333	664	1333	Mb/s
	SBVA484	Single rank component	664	1066	664	1066	664	1066	Mb/s
		1 rank DIMM[(1)(2)]	664	1066	664	1066	664	1066	Mb/s
		2 rank DIMM[(1)(3)]	664	1066	664	1066	664	1066	Mb/s
DDR3L	All FFV packages, FBVB900 and SFVC784	Single rank component	664	1866	664	1866	664	1866	Mb/s
		1 rank DIMM[(1)(2)]	664	1600	664	1600	664	1600	Mb/s
		2 rank DIMM[(1)(3)]	664	1333	664	1333	664	1333	Mb/s
	SFVA625	Single rank component	664	1600	664	1600	664	1600	Mb/s
		1 rank DIMM[(1)(2)]	664	1333	664	1333	664	1333	Mb/s
		2 rank DIMM[(1)(3)]	664	1066	664	1066	664	1066	Mb/s
	SBVA484	Single rank component	664	1066	664	1066	664	1066	Mb/s
		1 rank DIMM[(1)(2)]	664	1066	664	1066	664	1066	Mb/s
		2 rank DIMM[(1)(3)]	664	1066	664	1066	664	1066	Mb/s
LPDDR3	All FFV packages, FBVB900 and SFVC784	Single die package[(6)]	664	1600	664	1600	664	1600	Mb/s
		Dual die package[(6)]	664	1333	664	1333	664	1333	Mb/s
	SFVA625	Single die package[(6)]	664	1333	664	1333	664	1333	Mb/s
		Dual die package[(6)]	664	1066	664	1066	664	1066	Mb/s
	SBVA484	Single die package[(6)]	664	1066	664	1066	664	1066	Mb/s
		Dual die package[(6)]	664	1066	664	1066	664	1066	Mb/s

Notes:

1. Dual in-line memory module (DIMM) includes RDIMM, SODIMM, and UDIMM.
2. Includes: 1 rank 1 slot, dual-die package 2 rank.
3. Includes: 2 rank 1 slot.
4. Dual die package includes single die with ECC.
5. LPDDR4 support is only available as a 32-bit interface.
6. 64-bit LPDDR3 interface performance values are defined without ECC support.

Table 31: **PS NAND NV-DDR Synchronous Performance**

Memory Standard	Mode	Speed Grade			Units
		-3	-2	-1	
		Max	Max	Max	
NV-DDR[1]	5	200	200	200	Mb/s
	4	166.6	166.6	166.6	Mb/s
	3	133.3	133.3	133.3	Mb/s
	2	100	100	100	Mb/s
	1	66.6	66.6	66.6	Mb/s
	0	40	40	40	Mb/s

Notes:

1. The PS NAND memory controller interface for NV-DDR switching characteristics meets the requirements of the ONFI 3.1 specification.

Table 32: **PS NAND SDR Asynchronous Performance**

Memory Standard	Mode	Speed Grade			Units
		-3	-2	-1	
		Max	Max	Max	
SDR[1][2]	5	50	50	50	Mb/s
	4	40	40	40	Mb/s
	3	33.3	33.3	33.3	Mb/s
	2	28.5	28.5	28.5	Mb/s
	1	20	20	20	Mb/s
	0	10	10	10	Mb/s

Notes:

1. The PS NAND memory controller interface for SDR switching characteristics meets the requirements of the ONFI 3.1 specification.
2. The NAND controller reference clock frequency maximum is 83 MHz.

Table 33: **PS-PL Interface Performance**

Symbol	Description	Min	Max	Units
$F_{EMIOGEMCLK}$	EMIO gigabit Ethernet controller maximum frequency.	–	125	MHz
$F_{EMIOSDCLK}$	EMIO SD controller maximum frequency.	–	25	MHz
$F_{EMIOSPICLK}$	EMIO SPI controller maximum frequency.	–	25	MHz
$F_{EMIOTRACECLK}$	EMIO trace controller maximum frequency.	–	125	MHz
$F_{FCIDMACLK}$	Flow control interface DMA maximum frequency.	–	333	MHz
F_{AXICLK}	Maximum AXI interface performance.	–	333	MHz
$F_{DPLIVEVIDEO}$	DisplayPort controller live video interface maximum frequency.	–	300	MHz

PS Interface Specifications

PS Quad-SPI Controller Interface

Table 41: **Generic Quad-SPI Interface[(1)]**

Symbol	Description	Load Conditions[(2)]	Min	Max	Units
Quad-SPI device clock frequency operating at 150 MHz. Loopback enabled. LVCMOS 1.8V I/O standard.					
$T_{DCQSPICLK1}$	Quad-SPI clock duty cycle.	15 pF	45	55	%
$T_{QSPISSSCLK1}$	Slave select asserted to next clock edge.	15 pF	5.0	–	ns
$T_{QSPISCLKSS1}$	Clock edge to slave select deasserted.	15 pF	5.0	–	ns
$T_{QSPICKO1}$	Clock to output delay, all outputs.	15 pF	2.9	4.5	ns
$T_{QSPIDCK1}$	Setup time, all inputs.	15 pF	0.9	–	ns
$T_{QSPICKD1}$	Hold time, all inputs.	15 pF	1.0	–	ns
$F_{QSPICLK1}$	Quad-SPI device clock frequency.	15 pF	–	150	MHz
$F_{QSPIREFCLK1}$	Quad-SPI reference clock frequency.	15 pF	–	300	MHz
Quad-SPI device clock frequency operating at 100 MHz. Loopback enabled. LVCMOS 1.8V I/O standard.					
$T_{DCQSPICLK2}$	Quad-SPI clock duty cycle.	15 pF	45	55	%
		30 pF	45	55	%
$T_{QSPISSSCLK2}$	Slave select asserted to next clock edge.	15 pF	5.0	–	ns
		30 pF	5.0	–	ns
$T_{QSPISCLKSS2}$	Clock edge to slave select deasserted.	15 pF	5.0	–	ns
		30 pF	5.0	–	ns
$T_{QSPICKO2}$	Clock to output delay, all outputs.	15 pF	3.2	7.4	ns
		30 pF	3.2	7.4	ns
$T_{QSPIDCK2}$	Setup time, all inputs.	15 pF	2.3	–	ns
		30 pF	2.3	–	ns
$T_{QSPICKD2}$	Hold time, all inputs.	15 pF	0.0	–	ns
		30 pF	0.0	–	ns
$F_{QSPICLK2}$	Quad-SPI device clock frequency.	15 pF	–	100	MHz
		30 pF	–	100	MHz
$F_{QSPIREFCLK2}$	Quad-SPI reference clock frequency.	15 pF	–	200	MHz
		30 pF	–	200	MHz

Notes:

1. The test conditions are configured for the generic Quad-SPI interface at 150/100 MHz with a 12 mA drive strength and fast slew rate.
2. 30 pF loads are for dual-parallel stacked or stacked modes.

PS Gigabit Ethernet Controller Interface

Table 44: **RGMII Interface[(1)]**

Symbol	Description	Min	Max	Units
$T_{DCGEMTXCLK}$	Transmit clock duty cycle.	45	55	%
$T_{GEMTXCKO}$	TXD output clock to out time.	–0.5	0.5	ns
$T_{GEMRXDCK}$	RXD input setup time.	0.8	–	ns
$T_{GEMRXCKD}$	RXD input hold time.	0.8	–	ns
$T_{MDIOCLK}$	MDC output clock period.	400	–	ns
$T_{MDIOCKL}$	MDC low time.	160	–	ns
$T_{MDIOCKH}$	MDC high time.	160	–	ns
$T_{MDIODCK}$	MDIO input data setup time.	80	–	ns
$T_{MDIOCKD}$	MDIO input data hold time.	0.0	–	ns
$T_{MDIOCKO}$	MDIO output data delay time.	–1.0	15	ns
$F_{GETXCLK}$	RGMII_TX_CLK transmit clock frequency.	–	125	MHz
$F_{GERXCLK}$	RGMII_RX_CLK receive clock frequency.	–	125	MHz
$F_{ENET\_REF\_CLK}$	Ethernet reference clock frequency.	–	125	MHz

Notes:

1. The test conditions are configured to the LVCMOS 2.5V I/O standard with a 12 mA drive strength, fast slew rate, and a 15 pF load.

PS SD/SDIO Controller Interface

Table 45: **SD/SDIO Interface[(1)]**

Symbol	Description	Min	Max	Units
SD/SDIO Interface DDR50 Mode				
$T_{DCDDRCLK}$	SD device clock duty cycle.	45	55	%
$T_{SDDDRCKO1}$	Clock to output delay, data.[(2)]	1.0	6.8	ns
$T_{SDDRIVW}$	Input valid data window.[(3)]	3.5	–	ns
$T_{SDDDRDCK2}$	Input setup time, command.	4.7	–	ns
$T_{SDDDRCKD2}$	Input hold time, command.	1.5	–	ns
$T_{SDDDRCKO2}$	Clock to output delay, command.	1.0	13.8	ns
$F_{SDDDRCLK}$	High-speed mode SD device clock frequency.	–	50	MHz
SD/SDIO Interface SDR104				
$T_{DCSDHSCLK1}$	SD device clock duty cycle.	40	60	%
$T_{SDSDRCKO1}$	Clock to output delay, all outputs.[(2)]	1.0	3.2	ns
$T_{SDSDR1IVW}$	Input valid data window.[(3)]	0.5	–	UI
$F_{SDSDRCLK1}$	SDR104 mode device clock frequency.	–	200	MHz
SD/SDIO Interface SDR50/25				
$T_{DCSDHSCLK2}$	SD device clock duty cycle.	40	60	%
$T_{SDSDRCKO2}$	Clock to output delay, all outputs.[(2)]	1.0	6.8	ns
$T_{SDSDR2IVW}$	Input valid data window.[(3)]	0.3	–	UI

PS-GTR Transceiver

Table 56: **PS-GTR Transceiver DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
DV_{PPIN}	Differential peak-to-peak input voltage (external AC coupled).		100	–	1200	mV
V_{IN}	Single-ended input voltage. Voltage measured at the pin referenced to GND.		75	–	$V_{PS\_MGTRAVCC}$	mV
V_{CMIN}	Common mode input voltage.		–	0	–	mV
D_{VPPOUT}	Differential peak-to-peak output voltage.(1)	Transmitter output swing is set to maximum value.	800	–	–	mV
$V_{CMOUTAC}$	Common mode output voltage: AC coupled (equation based).		$V_{PS\_MGTRAVCC} – D_{VPPOUT}/2$			mV
R_{IN}	Differential input resistance.		–	100	–	Ω
R_{OUT}	Differential output resistance.		–	100	–	Ω
$R_{MGTRREF}$	Resistor value between calibration resistor pin to GND.		497.5	500	502.5	Ω
T_{OSKEW}	Transmitter output pair (TXP and TXN) intra-pair skew (All packages).		–	–	20	ps
C_{EXT}	Recommended external AC coupling capacitor.(2)		–	100	–	nF

Notes:

1. The output swing and pre-emphasis levels are programmable using the attributes discussed in the *Zynq UltraScale+ MPSoC Technical Reference Manual* (UG1085), and can result in values lower than reported in this table.
2. Other values can be used as appropriate to conform to specific protocols and standards.

Table 57: **PS-GTR Transceiver Clock DC Input Level Specification**

Symbol	DC Parameter	Min	Typ	Max	Units
V_{IDIFF}	Differential peak-to-peak input voltage.	250	–	2000	mV
R_{IN}	Differential input resistance.	–	100	–	Ω
C_{EXT}	Required external AC coupling capacitor.	–	10	–	nF

Table 58: **PS-GTR Transceiver Performance**

Symbol	Description	Speed Grade			Units
		-3	-2	-1	
F_{GTRMAX}	PS-GTR maximum line rate.	6.0	6.0	6.0	Gb/s
F_{GTRMIN}	PS-GTR minimum line rate.	1.25	1.25	1.25	Gb/s

Table 59: **PS-GTR Transceiver PLL/Lock Time Adaptation**

Symbol	Description	Min	Typ	Max	Units
T_{LOCK}	Initial PLL lock.	–	–	0.11	ms
T_{DLOCK}	Clock recovery phase acquisition and adaptation time.	–	–	24×10^6	UI

Programmable Logic (PL) Performance Characteristics

This section provides the performance characteristics of some common functions and designs implemented in Zynq UltraScale+ MPSoC. These values are subject to the same guidelines as the AC Switching Characteristics, page 22. In each table, the I/O bank type is either high performance (HP) or high density (HD).

Table 70: **LVDS Component Mode Performance**

Description	I/O Bank Type	Speed Grade and V_{CCINT} Operating Voltages										Units
		0.90V		0.85V				0.72V				
		-3		-2		-1		-2		-1		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
LVDS TX DDR (OSERDES 4:1, 8:1)	HP	0	1250	0	1250	0	1250	0	1250	0	1250	Mb/s
LVDS TX SDR (OSERDES 2:1, 4:1)	HP	0	625	0	625	0	625	0	625	0	625	Mb/s
LVDS RX DDR (ISERDES 1:4, 1:8)(1)	HP	0	1250	0	1250	0	1250	0	1250	0	1250	Mb/s
LVDS RX DDR	HD	0	250	0	250	0	250	0	250	0	250	Mb/s
LVDS RX SDR (ISERDES 1:2, 1:4)(1)	HP	0	625	0	625	0	625	0	625	0	625	Mb/s
LVDS RX SDR	HD	0	125	0	125	0	125	0	125	0	125	Mb/s

Notes:

1. LVDS receivers are typically bounded with certain applications to achieve maximum performance. Package skews are not included and should be removed through PCB routing.

Table 71: **LVDS Native Mode Performance(1)(2)**

Description	DATA_WIDTH	I/O Bank Type	Speed Grade and V_{CCINT} Operating Voltages										Units
			0.90V		0.85V				0.72V				
			-3(3)		-2(3)		-1		-2(3)		-1		
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
LVDS TX DDR (TX_BITSLICE)	4	HP	375	1600	375	1600	375	1260	375	1400	375	1260	Mb/s
	8		375	1600	375	1600	375	1260	375	1600	375	1260	Mb/s
LVDS TX SDR (TX_BITSLICE)	4	HP	187.5	800	187.5	800	187.5	630	187.5	700	187.5	630	Mb/s
	8		187.5	800	187.5	800	187.5	630	187.5	800	187.5	630	Mb/s
LVDS RX DDR (RX_BITSLICE)(4)	4	HP	375	1600	375	1600	375	1260	375	1400	375	1260	Mb/s
	8		375	1600	375	1600	375	1260	375	1600	375	1260	Mb/s
LVDS RX SDR (RX_BITSLICE)(4)	4	HP	187.5	800	187.5	800	187.5	630	187.5	700	187.5	630	Mb/s
	8		187.5	800	187.5	800	187.5	630	187.5	800	187.5	630	Mb/s

Notes:

1. Native mode is supported through the High-Speed SelectIO Interface Wizard available with the Vivado Design Suite. The performance values assume a source-synchronous interface.
2. PLL settings can restrict the minimum allowable data rate. For example, when using the PLL with CLKOUTPHY_MODE = VCO_HALF the minimum frequency is $PLL\_F_{VCOMIN}/2$.
3. In the SBVA484 package, the maximum data rate is 1260 Mb/s for DDR interfaces and 630 Mb/s for SDR interfaces.
4. LVDS receivers are typically bounded with certain applications to achieve maximum performance. Package skews are not included and should be removed through PCB routing.

Input Delay Measurement Methodology

Table 78 shows the test setup parameters used for measuring input delay.

Table 78: **Input Delay Measurement Methodology**

Description	I/O Standard Attribute	V_L (1)(2)	V_H (1)(2)	V_{MEAS} (1)(4)(6)	V_{REF} (1)(3)(5)
LVCMOS, 1.2V	LVCMOS12	0.1	1.1	0.6	–
LVCMOS, LVDCI, HSLVDCI, 1.5V	LVCMOS15, LVDCI_15, HSLVDCI_15	0.1	1.4	0.75	–
LVCMOS, LVDCI, HSLVDCI, 1.8V	LVCMOS18, LVDCI_18, HSLVDCI_18	0.1	1.7	0.9	–
LVCMOS, 2.5V	LVCMOS25	0.1	2.4	1.25	–
LVCMOS, 3.3V	LVCMOS33	0.1	3.2	1.65	–
LVTTL, 3.3V	LVTTL	0.1	3.2	1.65	–
HSTL (high-speed transceiver logic), class I, 1.2V	HSTL_I_12	V_{REF} – 0.25	V_{REF} + 0.25	V_{REF}	0.6
HSTL, class I, 1.5V	HSTL_I	V_{REF} – 0.325	V_{REF} + 0.325	V_{REF}	0.75
HSTL, class I, 1.8V	HSTL_I_18	V_{REF} – 0.4	V_{REF} + 0.4	V_{REF}	0.9
HSUL (high-speed unterminated logic), 1.2V	HSUL_12	V_{REF} – 0.25	V_{REF} + 0.25	V_{REF}	0.6
SSTL12 (stub series terminated logic), 1.2V	SSTL12	V_{REF} – 0.25	V_{REF} + 0.25	V_{REF}	0.6
SSTL135 and SSTL135 class II, 1.35V	SSTL135, SSTL135_II	V_{REF} – 0.2875	V_{REF} + 0.2875	V_{REF}	0.675
SSTL15 and SSTL15 class II, 1.5V	SSTL15, SSTL15_II	V_{REF} – 0.325	V_{REF} + 0.325	V_{REF}	0.75
SSTL18, class I and II, 1.8V	SSTL18_I, SSTL18_II	V_{REF} – 0.4	V_{REF} + 0.4	V_{REF}	0.9
POD10, 1.0V	POD10	V_{REF} – 0.2	V_{REF} + 0.2	V_{REF}	0.7
POD12, 1.2V	POD12	V_{REF} – 0.24	V_{REF} + 0.24	V_{REF}	0.84
DIFF_HSTL, class I, 1.2V	DIFF_HSTL_I_12	0.6 – 0.25	0.6 + 0.25	0(6)	–
DIFF_HSTL, class I, 1.5V	DIFF_HSTL_I	0.75 – 0.325	0.75 + 0.325	0(6)	–
DIFF_HSTL, class I, 1.8V	DIFF_HSTL_I_18	0.9 – 0.4	0.9 + 0.4	0(6)	–
DIFF_HSUL, 1.2V	DIFF_HSUL_12	0.6 – 0.25	0.6 + 0.25	0(6)	–
DIFF_SSTL, 1.2V	DIFF_SSTL12	0.6 – 0.25	0.6 + 0.25	0(6)	–
DIFF_SSTL135 and DIFF_SSTL135 class II, 1.35V	DIFF_SSTL135, DIFF_SSTL135_II	0.675 – 0.2875	0.675 + 0.2875	0(6)	–
DIFF_SSTL15 and DIFF_SSTL15 class II, 1.5V	DIFF_SSTL15, DIFF_SSTL15_II	0.75 – 0.325	0.75 + 0.325	0(6)	–
DIFF_SSTL18_I, DIFF_SSTL18_II, 1.8V	DIFF_SSTL18_I, DIFF_SSTL18_II	0.9 – 0.4	0.9 + 0.4	0(6)	–
DIFF_POD10, 1.0V	DIFF_POD10	0.5 – 0.2	0.5 + 0.2	0(6)	–
DIFF_POD12, 1.2V	DIFF_POD12	0.6 – 0.25	0.6 + 0.25	0(6)	–
LVDS (low-voltage differential signaling), 1.8V	LVDS	0.9 – 0.125	0.9 + 0.125	0(6)	–
LVDS_25, 2.5V	LVDS_25	1.25 – 0.125	1.25 + 0.125	0(6)	–

UltraRAM Switching Characteristics

The *UltraScale Architecture and Product Overview* (DS890) lists the Zynq UltraScale+ MPSoC that include this memory.

Table 81: **UltraRAM Switching Characteristics**

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
Maximum Frequency							
F_{MAX}	UltraRAM maximum frequency with OREG_B = True.	650	600	575	500	481	MHz
F_{MAX_ECC}	UltraRAM maximum frequency with OREG_B = False and EN_ECC_RD_B = True.	450	400	386	325	315	MHz
$F_{MAX\_NORPIPELINE}$	UltraRAM maximum frequency with OREG_B = False and EN_ECC_RD_B = False.	550	500	478	425	408	MHz
T_{PW} (1)	Minimum pulse width.	650	700	730	800	832	ps
T_{RSTPW}	Asynchronous reset minimum pulse width. One cycle required.	1 clock cycle					

Notes:

1. The MMCM and PLL DUTY_CYCLE attribute should be set to 50% to meet the pulse-width requirements at the higher frequencies.

Input/Output Delay Switching Characteristics

Table 82: **Input/Output Delay Switching Characteristics**

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
F_{REFCLK}	REFCLK frequency for IDELAYCTRL (component mode).	300 to 800					MHz
	REFCLK frequency for BITSLICE_CONTROL (native mode).(1)	300 to 2666.67	300 to 2666.67	300 to 2400	300 to 2400	300 to 2133	MHz
T_{MINPER_CLK}	Minimum period for IODELAY clock.	3.195	3.195	3.195	3.195	3.195	ns
T_{MINPER_RST}	Minimum reset pulse width.	52.00					ns
$T_{IDELAY\_RESOLUTION}$/ $T_{ODELAY\_RESOLUTION}$	IDELAY/ODELAY chain resolution.	2.1 to 12					ps

Notes:

1. PLL settings could restrict the minimum allowable data rate. For example, when using a PLL with CLKOUTPHY_MODE = VCO_HALF, the minimum frequency is PLL_FVCOMIN/2.

Table 92: **Sampling Window**

Description	Speed Grade and V_{CCINT} Operating Voltages					Units
	0.90V	0.85V		0.72V		
	-3	-2	-1	-2	-1	
T_{SAMP_BUFG}[1]	510	610	610	610	610	ps
$T_{SAMP\_NATIVE\_DPA}$	100	100	125	125	150	ps
$T_{SAMP\_NATIVE\_BISC}$	60	60	85	85	110	ps

Notes:

1. This parameter indicates the total sampling error of the Zynq UltraScale+ MPSoC DDR input registers, measured across voltage, temperature, and process. The characterization methodology uses the MMCM to capture the DDR input registers' edges of operation. These measurements include: CLK0 MMCM jitter, MMCM accuracy (phase offset), and MMCM phase shift resolution. These measurements do not include package or clock tree skew.

GTH Transceiver Specifications

The *UltraScale Architecture and Product Overview* (DS890) lists the Zynq UltraScale+ MPSoCs that include the GTH transceivers.

GTH Transceiver DC Input and Output Levels

Table 94 summarizes the DC specifications of the GTH transceivers in Zynq UltraScale+ MPSoC. Consult the *UltraScale Architecture GTH Transceiver User Guide* (UG576) for further details.

Table 94: **GTH Transceiver DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
D_{VPPIN}	Differential peak-to-peak input voltage (external AC coupled).	>10.3125 Gb/s	150	–	1250	mV
		6.6 Gb/s to 10.3125 Gb/s	150	–	1250	mV
		≤ 6.6 Gb/s	150	–	2000	mV
V_{IN}	Single-ended input voltage. Voltage measured at the pin referenced to GND.	DC coupled $V_{MGTAVTT}$ = 1.2V	–400	–	$V_{MGTAVTT}$	mV
V_{CMIN}	Common mode input voltage.	DC coupled $V_{MGTAVTT}$ = 1.2V	–	2/3 $V_{MGTAVTT}$	–	mV
D_{VPPOUT}	Differential peak-to-peak output voltage.(1)	Transmitter output swing is set to 11111	800	–	–	mV
$V_{CMOUTDC}$	Common mode output voltage: DC coupled (equation based).	When remote RX is terminated to GND	$V_{MGTAVTT}/2 – D_{VPPOUT}/4$			mV
		When remote RX termination is floating	$V_{MGTAVTT} – D_{VPPOUT}/2$			mV
		When remote RX is terminated to V_{RX_TERM}(2)	$V_{MGTAVTT} - \frac{D_{VPPOUT}}{4} - \left(\frac{V_{MGTAVTT} - V_{RX\_TERM}}{2}\right)$			mV
$V_{CMOUTAC}$	Common mode output voltage: AC coupled (equation based).		$V_{MGTAVTT} – D_{VPPOUT}/2$			mV
R_{IN}	Differential input resistance.		–	100	–	Ω
R_{OUT}	Differential output resistance.		–	100	–	Ω
T_{OSKEW}	Transmitter output pair (TXP and TXN) intra-pair skew (all packages).		–	–	10	ps
C_{EXT}	Recommended external AC coupling capacitor.(3)		–	100	–	nF

Notes:

1. The output swing and pre-emphasis levels are programmable using the attributes discussed in the *UltraScale Architecture GTH Transceiver User Guide* (UG576), and can result in values lower than reported in this table.
2. V_{RX_TERM} is the remote RX termination voltage.
3. Other values can be used as appropriate to conform to specific protocols and standards.

GTY Transceiver Specifications

The *UltraScale Architecture and Product Overview* (DS890) lists the Zynq UltraScale+ MPSoCs that include the GTY transceivers.

GTY Transceiver DC Input and Output Levels

Table 106 and Table 107 summarize the DC specifications of the GTY transceivers in Zynq UltraScale+ MPSoCs. Consult the *UltraScale Architecture GTY Transceiver User Guide* (UG578) for further details.

Table 106: **GTY Transceiver DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
DV_{PPIN}	Differential peak-to-peak input voltage (external AC coupled)	>10.3125 Gb/s	150	–	1250	mV
		6.6 Gb/s to 10.3125 Gb/s	150	–	1250	mV
		≤ 6.6 Gb/s	150	–	2000	mV
V_{IN}	Single-ended input voltage. Voltage measured at the pin referenced to GND.	DC coupled $V_{MGTAVTT}$ = 1.2V	–400	–	$V_{MGTAVTT}$	mV
V_{CMIN}	Common mode input voltage	DC coupled $V_{MGTAVTT}$ = 1.2V	–	2/3 $V_{MGTAVTT}$	–	mV
D_{VPPOUT}	Differential peak-to-peak output voltage(1)	Transmitter output swing is set to 11111	800	–	–	mV
$V_{CMOUTDC}$	Common mode output voltage: DC coupled (equation based)	When remote RX is terminated to GND	$V_{MGTAVTT}/2 – D_{VPPOUT}/4$			mV
		When remote RX termination is floating	$V_{MGTAVTT} – D_{VPPOUT}/2$			mV
		When remote RX is terminated to V_{RX_TERM}(2)	$V_{MGTAVTT} - \frac{D_{VPPOUT}}{4} - \left(\frac{V_{MGTAVTT} - V_{RX\_TERM}}{2}\right)$			mV
$V_{CMOUTAC}$	Common mode output voltage: AC coupled	Equation based	$V_{MGTAVTT} – D_{VPPOUT}/2$			mV
R_{IN}	Differential input resistance		–	100	–	Ω
R_{OUT}	Differential output resistance		–	100	–	Ω
T_{OSKEW}	Transmitter output pair (TXP and TXN) intra-pair skew		–	–	10	ps
C_{EXT}	Recommended external AC coupling capacitor(3)		–	100	–	nF

Notes:

1. The output swing and pre-emphasis levels are programmable using the GTY transceiver attributes discussed in the *UltraScale Architecture GTY Transceiver User Guide* (UG578) and can result in values lower than reported in this table.
2. V_{RX_TERM} is the remote RX termination voltage.
3. Other values can be used as appropriate to conform to specific protocols and standards.

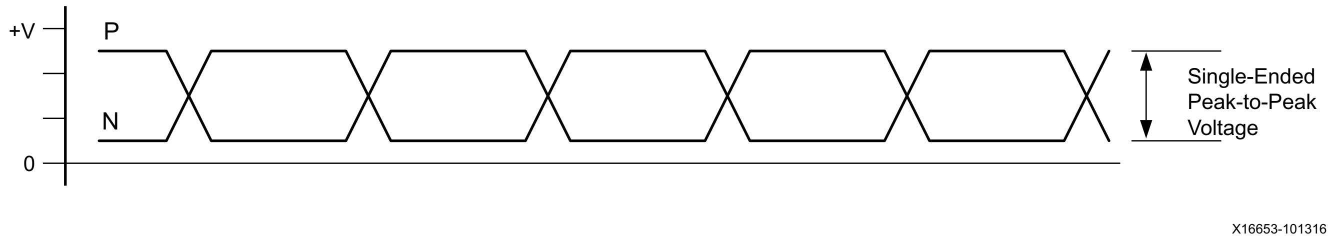

Figure 5: **Single-Ended Peak-to-Peak Voltage**

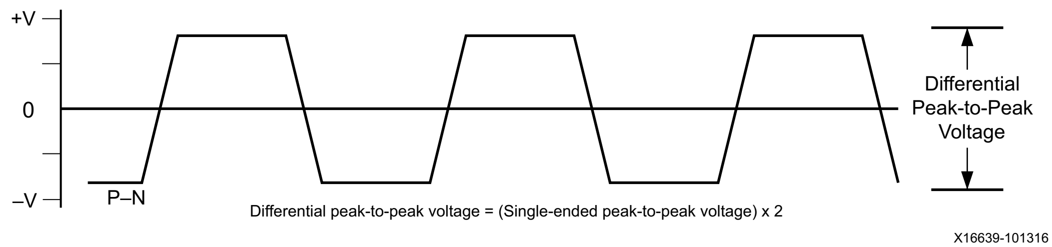

Figure 6: **Differential Peak-to-Peak Voltage**

Table 107 and Table 108 summarize the DC specifications of the clock input of the GTY transceivers in Zynq UltraScale+ MPSoCs. Consult the *UltraScale Architecture GTY Transceiver User Guide* (UG578) for further details.

Table 107: **GTY Transceiver Clock DC Input Level Specification**

Symbol	DC Parameter	Min	Typ	Max	Units
V_{IDIFF}	Differential peak-to-peak input voltage	250	–	2000	mV
R_{IN}	Differential input resistance	–	100	–	Ω
C_{EXT}	Required external AC coupling capacitor	–	10	–	nF

Table 108: **GTY Transceiver Clock Output Level Specification**

Symbol	Description	Conditions	Min	Typ	Max	Units
V_{OL}	Output Low voltage for P and N	R_T = 100Ω across P and N signals	100	–	330	mV
V_{OH}	Output High voltage for P and N	R_T = 100Ω across P and N signals	500	–	700	mV
V_{DDOUT}	Differential output voltage (P–N), P = High (N–P), N = High	R_T = 100Ω across P and N signals	300	–	430	mV
V_{CMOUT}	Common mode voltage	R_T = 100Ω across P and N signals	300	–	500	mV

Table 113: **GTY Transceiver PLL/Lock Time Adaptation**

Symbol	Description	Conditions	All Speed Grades			Units
			Min	Typ	Max	
T_{LOCK}	Initial PLL lock.		–	–	1	ms
T_{DLOCK}	Clock recovery phase acquisition and adaptation time for decision feedback equalizer (DFE).	After the PLL is locked to the reference clock, this is the time it takes to lock the clock data recovery (CDR) to the data present at the input.	–	50,000	37 x 10^6	UI
	Clock recovery phase acquisition and adaptation time for low-power mode (LPM) when the DFE is disabled.		–	50,000	2.3 x 10^6	UI

Table 114: **GTY Transceiver User Clock Switching Characteristics[1]**

Symbol	Description	Data Width Conditions (Bit)		Speed Grade and V_{CCINT} Operating Voltages					Units
				0.90V	0.85V		0.72V		
		Internal Logic	Interconnect Logic	-3[2]	-2[2][3]	-1[4][5]	-2[3]	-1[5]	
$F_{TXOUTPMA}$	TXOUTCLK maximum frequency sourced from OUTCLKPMA			511.719	511.719	402.833	402.833	322.266	MHz
$F_{RXOUTPMA}$	RXOUTCLK maximum frequency sourced from OUTCLKPMA			511.719	511.719	402.833	402.833	322.266	MHz
$F_{TXOUTPROGDIV}$	TXOUTCLK maximum frequency sourced from TXPROGDIVCLK			511.719	511.719	511.719	511.719	511.719	MHz
$F_{RXOUTPROGDIV}$	RXOUTCLK maximum frequency sourced from RXPROGDIVCLK			511.719	511.719	511.719	511.719	511.719	MHz
F_{TXIN}	TXUSRCLK[6] maximum frequency	16	16, 32	511.719	511.719	390.625	390.625	322.266	MHz
		32	32, 64	511.719	511.719	390.625	390.625	322.266	MHz
		64	64, 128	511.719	440.781	402.832	402.832	195.313	MHz
		20	20, 40	409.375	409.375	312.500	312.500	257.813	MHz
		40	40, 80	409.375	409.375	312.500	350.000	257.813	MHz
		80	80, 160	409.375	352.625	322.266	352.625	156.250	MHz
F_{RXIN}	RXUSRCLK[6] maximum frequency	16	16, 32	511.719	511.719	390.625	390.625	322.266	MHz
		32	32, 64	511.719	511.719	390.625	390.625	322.266	MHz
		64	64, 128	511.719	440.781	402.832	402.832	195.313	MHz
		20	20, 40	409.375	409.375	312.500	312.500	257.813	MHz
		40	40, 80	409.375	409.375	312.500	350.000	257.813	MHz
		80	80, 160	409.375	352.625	322.266	352.625	156.250	MHz

Integrated Interface Block for 100G Ethernet MAC and PCS

More information and documentation on solutions using the integrated 100 Gb/s Ethernet block can be found at UltraScale+ Integrated 100G Ethernet MAC/PCS. The *UltraScale Architecture and Product Overview* (DS890) lists how many blocks are in each Zynq UltraScale+ MPSoC.

Table 121: **Maximum Performance for 100G Ethernet Designs**

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2[1]	-1	-2	-1[2]	
F_{TX_CLK}	Transmit clock	390.625	390.625	322.223	322.223	322.223	MHz
F_{RX_CLK}	Receive clock	390.625	390.625	322.223	322.223	322.223	MHz
$F_{RX\_SERDES\_CLK}$	Receive serializer/deserializer clock	390.625	390.625	322.223	322.223	322.223	MHz
F_{DRP_CLK}	Dynamic reconfiguration port clock	250.00	250.00	250.00	250.00	250.00	MHz

Notes:

1. The maximum clock frequency of 390.625 MHz only applies to the CAUI-10 interface. The maximum clock frequency for the CAUI-4 interface is 322.223 MHz.
2. The CAUI-4 interface is not supported by -1L speed grade devices where V_{CCINT}=0.72V.

Integrated Interface Block for PCI Express Designs

More information and documentation on solutions for PCI Express designs can be found at PCI Express. The *UltraScale Architecture and Product Overview* (DS890) lists the Zynq UltraScale+ MPSoCs that include this block.

Table 122: **Maximum Performance for PCI Express Designs**[1][2]

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
$F_{PIPECLK}$	Pipe clock maximum frequency.	250.00	250.00	250.00	250.00	250.00	MHz
$F_{CORECLK}$	Core clock maximum frequency.	500.00	500.00	500.00	250.00	250.00	MHz
F_{DRPCLK}	DRP clock maximum frequency.	250.00	250.00	250.00	250.00	250.00	MHz
$F_{MCAPCLK}$	MCAP clock maximum frequency.	125.00	125.00	125.00	125.00	125.00	MHz

Notes:

1. PCI Express Gen4 operation is supported for x1, x2, x4, and x8 widths.
2. PCI Express Gen4 operation is supported in -3E, -2E, and -2I speed grades.

Table 124: **PL SYSMON Specifications *(Cont'd)***

Parameter	Symbol	Comments/Conditions	Min	Typ	Max	Units
On-Chip Sensor Accuracy						
Temperature sensor error[1][3]		T_j = –55°C to 125°C (with external REF)	–	–	±3	°C
		T_j = –55°C to 110°C (with internal REF)	–	–	±3.5	°C
		T_j = 110°C to 125°C (with internal REF)	–	–	±5	°C
Supply sensor error[4]		Supply voltages 0.72V to 1.2V, T_j = –40°C to 100°C (with external REF)	–	–	±0.5	%
		Supply voltages 0.72V to 1.2V, T_j = –55°C to 125°C (with external REF)	–	–	±1.0	%
		All other supply voltages, T_j = –40°C to 100°C (with external REF)	–	–	±1.0	%
		All other supply voltages, T_j = –55°C to 125°C (with external REF)	–	–	±2.0	%
		Supply voltages 0.72V to 1.2V, T_j = –40°C to 100°C (with internal REF)	–	–	±1.0	%
		Supply voltages 0.72V to 1.2V, T_j = –55°C to 125°C (with internal REF)	–	–	±2.0	%
		All other supply voltages, T_j = –40°C to 100°C (with internal REF)	–	–	±1.5	%
		All other supply voltages, T_j = –55°C to 125°C (with internal REF)	–	–	±2.5	%
Conversion Rate[5]						
Conversion time—continuous	t_{CONV}	Number of ADCCLK cycles	26	–	32	Cycles
Conversion time—event	t_{CONV}	Number of ADCCLK cycles	–	–	21	Cycles
DRP clock frequency	DCLK	DRP clock frequency	8	–	250	MHz
ADC clock frequency	ADCCLK	Derived from DCLK	1	–	5.2	MHz
DCLK duty cycle			40	–	60	%
SYSMON Reference[6]						
External reference	V_{REFP}	Externally supplied reference voltage	1.20	1.25	1.30	V
On-chip reference		Ground V_{REFP} pin to AGND, T_j = –40°C to 100°C	1.2375	1.25	1.2625	V
		Ground V_{REFP} pin to AGND, T_j = –55°C to 125°C	1.225	1.25	1.275	V

Notes:

1. ADC offset errors are removed by enabling the ADC automatic offset calibration feature. The values are specified for when this feature is enabled.
2. See the *Analog Input* section in the *UltraScale Architecture System Monitor User Guide* (UG580).
3. When reading temperature values directly from the PMBus interface, the SYSMON has a +4°C offset due to the transfer function used by the PMBus application. For example, the external REF temperature sensor error's range of ±3°C becomes +1°C to +7°C when the temperature is read through the PMBus interface.
4. Supply sensor offset and gain errors are removed by enabling the automatic offset and gain calibration feature. The values are specified for when this feature is enabled.
5. See the *Adjusting the Acquisition Settling Time* section in the *UltraScale Architecture System Monitor User Guide* (UG580).
6. Any variation in the reference voltage from the nominal V_{REFP} = 1.25V and V_{REFN} = 0V will result in a deviation from the ideal transfer function. This also impacts the accuracy of the internal sensor measurements (i.e., temperature and power supply). However, for external ratiometric type applications allowing reference to vary by ±4% is permitted.